

*9/1*  
*crossed*  

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irradiating an intense light to said insulating film; and  
forming a gate electrode on said insulating film.

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*9/2*  

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6. (Four Times Amended) A method for manufacturing a thin film transistor comprising the steps of:

forming a semiconductor film comprising amorphous silicon over a substrate;  
crystallizing said semiconductor film by irradiating a laser light;  
 patterning the crystallized semiconductor film to form first and second semiconductor islands;  
 forming an insulating film comprising silicon oxide on each of said first and second semiconductor islands by a vapor phase deposition using TEOS at a temperature of 200 to 400°C.; and  
 *F*  
 irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas.

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*9/3*  

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11. (Four Times Amended) A method for manufacturing a thin film transistor comprising the steps of:

forming a semiconductor film comprising amorphous silicon over a substrate;  
crystallizing said semiconductor film by irradiating a laser light;  
 patterning the crystallized semiconductor film to form first and second semiconductor islands;  
 forming an insulating film comprising silicon oxide on each of said first and second semiconductor islands by a vapor phase deposition using TEOS at a temperature of 200 to 400° C.;  
 irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas; and  
 forming a gate electrode on said insulating film;

93  
revised

introducing phosphorus into said first and second semiconductor islands; and introducing boron into said second semiconductor island,  
wherein a dose amount of said boron is larger than that of said phosphorus.

94

30. (Four Times Amended) A method for manufacturing a thin film transistor comprising the steps of:

forming a crystalline semiconductor film over a substrate;  
patterning the crystallized semiconductor film to form first and second semiconductor islands;  
forming an insulating film comprising silicon oxide on each of said first and second semiconductor islands by a vapor phase deposition using TEOS at a temperature of 200 to 400° C.;  
irradiating an intense light to said insulating film;  
forming a gate electrode on said insulating film;  
introducing phosphorus into said first and second semiconductor islands; and introducing boron into said second semiconductor island,  
wherein a dose amount of said boron is larger than that of said phosphorus.

95

34. (Four Times Amended) A method for manufacturing a thin film transistor comprising the steps of:

forming a crystalline semiconductor film over a substrate;  
patterning the crystallized semiconductor film to form first and second semiconductor islands;  
forming an insulating film comprising silicon oxide on each of said first and second semiconductor islands by a vapor phase deposition using TEOS at a temperature of 200 to 400° C.;  
irradiating an intense light to said insulating film in an atmosphere comprising an